

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

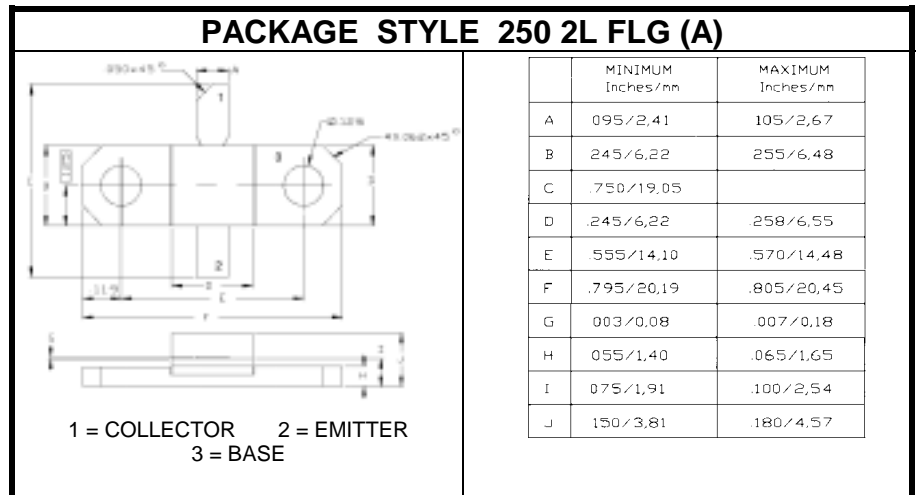
The **ASI SD1526-08** is a Common Base Device Designed for IFF, DME, and Tacan Pulse Applications.

**FEATURES INCLUDE:**

- Gold Metalization
- Input Matching
- Low Thermal Resistance

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	1.0 A
<b>V<sub>CE</sub></b>	45 V
<b>P<sub>DISS</sub></b>	21.9 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +150 °C
<b>θ<sub>JC</sub></b>	8.0 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1.0 mA	45			V
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 5.0 mA	45			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 5.0 mA	45			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 28 V			1.0	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 100 mA	10		200	---
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 28 V    P <sub>out</sub> = 5.0 W PULSE WIDTH = 10 μS	9.5			dB
	f = 1025 to 1150 MHz DUTY CYCLE = 1.0%				